

Murat Soylu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	The photovoltaic application and optics of ZnO/CdO and ZnO/NiO nanocomposite binary system. , 2022, 165, 207190.		4
2	EFFECT OF DOPING THIOUREA IN CdO THIN FILMS FOR ELECTRONIC APPLICATIONS. Surface Review and Letters, 2022, 29, .	1.1	0
3	Dopant-induced photoresponsivity in coumarin-dye-sensitized nanowire NiO/p-Si heterojunction. Materials Science in Semiconductor Processing, 2020, 106, 104784.	4.0	6
4	Solution molarity dependent structural and optical properties of CdO nanostructured thin films. Optik, 2020, 216, 164865.	2.9	12
5	A Temperature Sensor Based on Al/p-Si/CuCdO ₂ /Al Diode for Low Temperature Applications. Journal of Electronic Materials, 2020, 49, 2317-2325.	2.2	8
6	The effect of molar ratio on the photo-generated charge activity of ZnO/CdO composites. European Physical Journal Plus, 2020, 135, 1.	2.6	5
7	Solar light sensitive photodiode produced using a coumarin doped bismuth oxide composite. Materials Science in Semiconductor Processing, 2019, 90, 129-142.	4.0	31
8	Controlling the properties of ZnO thin films by varying precursor concentration. Journal of Alloys and Compounds, 2018, 741, 957-968.	5.5	26
9	Optoelectrical properties of Al/p-Si/Fe:N doped ZnO/Al diodes. Thin Solid Films, 2018, 653, 236-248.	1.8	23
10	Ruthenium(II) Complex Based Photodiode for Organic Electronic Applications. Journal of Electronic Materials, 2018, 47, 828-833.	2.2	35
11	Effect of calcination and carbon incorporation on NiO nanowires for photodiode performance. Microelectronic Engineering, 2018, 202, 51-59.	2.4	19
12	n-GaAs diode with photoresponsivity based on 3-aminorhodanine thin films. Applied Optics, 2018, 57, 6788.	1.8	3
13	Investigating the coumarin capability in chalcogenide 20Ti ₂ Se/Cd ₈₀ Pr ₂ Se ₃ system based photovoltaics. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2018, 202, 123-130.	3.9	1
14	Composite CuFe _{1-x} Sn _x O ₂ / p -type silicon photodiodes. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2017, 180, 110-118.	3.9	14
15	The validity of Kohlrausch law for the photocurrent transient and the role of N ₂ /Ar flow ratio in photoconductivity of sputtered CoZnO. Journal of Alloys and Compounds, 2017, 712, 152-163.	5.5	10
16	Dye based photodiodes for solar energy applications. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	14
17	Analysis of photoconductive mechanisms of organic-on-inorganic photodiodes. Physica E: Low-Dimensional Systems and Nanostructures, 2017, 93, 284-290.	2.7	12
18	CdO thin films based on the annealing temperature differences prepared by sol-gel method and their heterojunction devices. Materials Research Express, 2017, 4, 126307.	1.6	11

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19	Surface coating of ZnO nanoparticles onto 6H-SiC(0001): Temperature-dependent rectifying behavior. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2016, 78, 85-91.	2.7	1
20	Thermally activated conductivity of Si hybrid structure based on ZnPc thin film. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	2.3	2
21	Temperature-dependent model for hole transport mechanism in a poly(1.8-diaminocarbazole)/Si structure. <i>Philosophical Magazine</i> , 2016, 96, 2600-2614.	1.6	3
22	Photodiode Based on CdO Thin Films as Electron Transport Layer. <i>Journal of Electronic Materials</i> , 2016, 45, 5756-5763.	2.2	26
23	Low leakage current of CdSe quantum dots/Si composite structure and its performance for photodiode and solar cell. <i>Ceramics International</i> , 2016, 42, 14949-14955.	4.8	5
24	Fabrication and characterization of light-sensing device based on transparent ZnO thin film prepared by sol-gel. <i>Optik</i> , 2016, 127, 8479-8486.	2.9	9
25	Analysis of photovoltaic behavior of Si-based junctions containing novel graphene oxide/nickel(II) phthalocyanine composite films. <i>Microelectronic Engineering</i> , 2016, 154, 53-61.	2.4	18
26	Correlations for coumarin additive on the electrical and photocatalytic activity of TiO ₂ modified by thiourea. <i>Microelectronic Engineering</i> , 2016, 154, 26-37.	2.4	10
27	Low-Temperature Electrical Characteristics of Si-Based Device with New Tetrakis NiPc-SNS Active Layer. <i>Journal of Electronic Materials</i> , 2016, 45, 411-417.	2.2	3
28	A novel photodiode based on Ruthenium(II) complex containing polydentate pyridine as photocatalyst. <i>Microelectronics Reliability</i> , 2015, 55, 2685-2688.	1.7	9
29	Transparent CdO/n-GaN(0001) heterojunction for optoelectronic applications. <i>Journal of Physics and Chemistry of Solids</i> , 2015, 85, 26-33.	4.0	36
30	Electrical and optical properties of ZnO/Si heterojunctions as a function of the Mg dopant content. <i>Materials Science in Semiconductor Processing</i> , 2015, 29, 76-82.	4.0	27
31	Study of optical and electrical assessments of the quaternary MgZnSnO system containing different Mg content. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 4235-4245.	2.2	17
32	Properties of sol-gel synthesized n-ZnO/n-GaN (0001) isotype heterojunction. <i>Materials Chemistry and Physics</i> , 2014, 143, 495-502.	4.0	11
33	GaAs heterojunction devices with MDMO-PPV thin films. <i>Vacuum</i> , 2014, 106, 33-38.	3.5	4
34	ZnO nanostructured thin films: Structural and optical properties controlled by ruthenium content. <i>Superlattices and Microstructures</i> , 2014, 67, 144-155.	3.1	7
35	The electrical characterization of ZnO/GaAs heterojunction diode. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014, 64, 240-245.	2.7	23
36	Rectifying structure with high voltage operation based on CuBO ₂ as an UV photocatalyst. <i>Journal of Alloys and Compounds</i> , 2014, 617, 602-608.	5.5	12

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37	Photoelectrical characterization of a new generation diode having GaFeO ₃ interlayer. Solar Energy Materials and Solar Cells, 2014, 124, 180-185.	6.2	54
38	Preparation of Tungsten Trioxide Nanorods by Hydrothermal Route: n-Tungsten Trioxide Nanorods/p-Silicon n-p Junction. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 327-333.	0.5	9
39	CdS Quantum Dots and Dye Co-Sensitized Nanorods TiO ₂ /Solar Cell. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 662-665.	0.5	7
40	Effects of Different TiO ₂ Solution Compositions on Efficiency of Quantum Dot Solar Cell (QDSC) by Sol-Gel Method. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 392-396.	0.5	0
41	Controlling of conduction mechanism and electronic parameters of silicon-metal junction by mixed Methylene Blue/2,7-dichlorofluorescein. Microelectronics Reliability, 2013, 53, 1901-1906.	1.7	21
42	Improvement of Efficiency in CdS Quantum Dots Sensitized Solar Cells. Acta Physica Polonica A, 2013, 124, 750-754.	0.5	2
43	On the energy distribution of interface states and their relaxation time profiles in Al/pentacene/p-GaAs heterojunction diode. Journal of Applied Physics, 2012, 111, 034508.	2.5	15
44	Effects of interface states and series resistance on electrical properties of Al/nanostructure CdO/p-GaAs diode. Journal of Alloys and Compounds, 2012, 541, 462-467.	5.5	37
45	Barrier height enhancement and temperature dependence of the electrical characteristics of Al Schottky contacts on p-GaAs with organic Rhodamine B interfacial layer. Superlattices and Microstructures, 2012, 52, 470-483.	3.1	14
46	Fabrication and electrical characteristics of Perylene-3,4,9,10-tetracarboxylic dianhydride/p-GaAs diode structure. Microelectronics Reliability, 2012, 52, 1355-1361.	1.7	10
47	Properties of PEDOT:PEG/ZnO/p-Si heterojunction diode. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 785-790.	3.5	13
48	Influence of illumination intensity and temperature on the electrical characteristics of an Al/p-GaAs/In structure prepared by thermal evaporation. Microelectronic Engineering, 2012, 99, 50-57.	2.4	25
49	Fabrication and characterization of transparent MEH-PPV/n-GaN (0001) heterojunction devices. Optical Materials, 2012, 34, 878-883.	3.6	6
50	Modification of electrical properties of Al/p-Si Schottky barrier device based on 2,7-dichlorofluorescein. Journal of Applied Physics, 2011, 110, .	2.5	24
51	Electrical characteristics of Au/Pyronine-B/moderately doped n-type InP Schottky structures in a wide temperature range. Journal of Alloys and Compounds, 2011, 509, 5105-5111.	5.5	12
52	The effect of thickness of organic layer on electronic properties of Al/Rhodamine B/p-Si structure. Materials Science in Semiconductor Processing, 2011, 14, 212-218.	4.0	22
53	Controlling of electronic parameters of GaAs Schottky diode by poly(3,4-ethylenedioxythiophene)-block-poly(ethylene glycol) organic interlayer. Microelectronic Engineering, 2011, 88, 867-871.	2.4	15
54	Photovoltaic and interface state density properties of the Au/n-GaAs Schottky barrier solar cell. Thin Solid Films, 2011, 519, 1950-1954.	1.8	45

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55	The effects of annealing on Au/pyronine-B/MD n-InP Schottky structure. Journal of Physics and Chemistry of Solids, 2010, 71, 1398-1403.	4.0	21
56	Analysing space charge-limited conduction in Au/n-InP Schottky diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 43, 534-538.	2.7	52
57	Analysis of barrier height inhomogeneity in Au/n-GaAs Schottky barrier diodes by Tung model. Journal of Alloys and Compounds, 2010, 506, 418-422.	5.5	45
58	Barrier characteristics of gold Schottky contacts on moderately doped n-InP based on temperature dependent I_A-V and C_A-V measurements. Microelectronic Engineering, 2009, 86, 88-95.	2.4	52